NSN 5962-01-369-6836

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Maximum Power Dissipation Rating:
1.04 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
An/fps-124
Features Provided:
Programmed and schottky
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Bipolar metal-oxide semiconductor
Case Outline Source And Designator:
D-3 mil-m-38510
Current Rating Per Characteristic:
100.00 milliamperes reverse current, dc
Terminal Surface Treatment:
Solder
Product Name:
Microcircuit, digital, schottky, bipolar 65, 536 bit (8k x 8) programmable read-only memory (prom), monolithic silicon
Voltage Rating And Type Per Characteristic:
-0.3 volts total supply and 7.0 volts total supply and 5.5 volts absolute input and 4.5 volts positive power supply span and 5.5 volts
positive power supply span
Time Rating Per Chacteristic:
55.00 nanoseconds access
Memory Device Type:
Prom

Hybrid Technology Type:

Monolithic

Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

24 printed circuit

Specification Data:

67268-82009 government standard and 56232-1219253 manufacturers specification control

Specification Or Standard:

02 type and j case and a finish and 227 number

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Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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